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CSD16321Q5

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N-Channel NexFET™ Power MOSFET

Check for Samples: CSD16321Q5

FEATURES

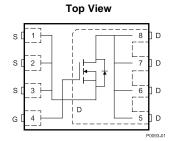
- Optimized for 5V Gate Drive
- Ultra Low Qg and Qgd
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- RoHS Compliant
- SON 5mm × 6mm Plastic Package

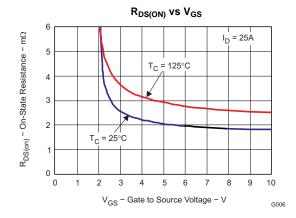
APPLICATIONS

- Point-of-Load Synchronous Buck Converter for Applications in Networking, Telecom and Computing Systems
- · Optimized for Synchronous FET Applications

DESCRIPTION

The NexFET™ power MOSFET has been designed to minimize losses in power conversion applications.





PRODUCT SUMMARY

V_{DS}	Drain to Source Voltage 25					
Q_g	Gate Charge Total (4.5V)	14	nC			
Q_{gd}	Gate Charge Gate to Drain	2.5	nC			
		$V_{GS} = 3V$	2.8	mΩ		
R _{DS(on)}	Drain to Source On Resistance	V _{GS} = 4.5V 2	2.1	mΩ		
		V _{GS} = 8V	1.9	mΩ		
$V_{GS(th)}$	Threshold Voltage	1.1	٧			

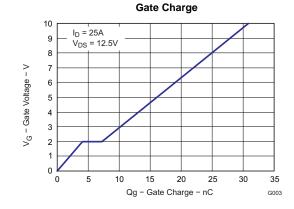
ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD16321Q5	SON 5 x 6 Plastic Package	13-inch reel	2500	Tape and Reel

ABSOLUTE MAXIMUM RATINGS

T _A = 2	5°C unless otherwise stated	VALUE	UNIT
V_{DS}	Drain to Source Voltage	25	٧
V_{GS}	Gate to Source Voltage	+10 / -8	٧
1	Continuous Drain Current, T _C = 25°C	100	Α
I _D	Continuous Drain Current(1)	31	Α
I_{DM}	Pulsed Drain Current, T _A = 25°C(2)	200	Α
P_D	Power Dissipation(1)	3.1	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C
E _{AS}	Avalanche Energy, single pulse I_D = 66A, L = 0.1mH, R_G = 25 Ω	218	mJ

- (1) Typical $R_{\theta JA}$ = 39°C/W on 1in^2 Cu (2 oz.) on 0.060" thick FR4 PCB.
- (2) Pulse width $\leq 300 \mu s$, duty cycle $\leq 2\%$



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

NexFET is a trademark of Texas Instruments.



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

	PARAMETER	METER TEST CONDITIONS		TYP	MAX	UNIT
Static Cl	haracteristics					
BV _{DSS}	Drain to Source Voltage	$V_{GS} = 0V, I_D = 250\mu A$	25			V
I _{DSS}	Drain to Source Leakage Current	V _{GS} = 0V, V _{DS} = 20V			1	μΑ
I _{GSS}	Gate to Source Leakage Current	V _{DS} = 0V, V _{GS} = +10 / -8V			100	nA
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.9	1.1	1.4	V
		$V_{GS} = 3V, I_{D} = 25A$		2.8	3.8	mΩ
R _{DS(on)}	Drain to Source On Resistance	$V_{GS} = 4.5V, I_D = 25A$		2.1	2.6	mΩ
gfs Dynamic C _{iss} C _{oss}		V _{GS} = 8V, I _D = 25A	2.8 2.1 1.9 150 2360 1700 115 1.5 14 2.5 4 2.1	1.9	2.4	mΩ
g _{fs}	Transconductance	$V_{DS} = 12.5V, I_{D} = 25A$	25 / 0.9 1.1 1.4 2.8 3.8 2.1 2.6 1.9 2.4 150 2360 3100 1700 2200 115 150 1.5 3 14 19 2.5 4 2.1 36 9 15 27 17 0.8 1 = 300Α/μs		S	
Dynamic	Characteristics		· -			
C _{iss}	Input Capacitance			2360	3100	pF
C _{oss}	Output Capacitance	$V_{GS} = 0V, V_{DS} = 12.5V,$ $f = 1MHz$		1700	2200	pF
C_{rss}	Reverse Transfer Capacitance			115	150	pF
R_G	Series Gate Resistance			1.5	3	Ω
Q_g	Gate Charge Total (4.5V)			14	19	nC
Q_{gd}	Gate Charge Gate to Drain	V _{DS} = 12.5V,		2.5		nC
Q_{gs}	Gate Charge Gate to Source	$I_D = 25A$		4		nC
$Q_{g(th)}$	Gate Charge at Vth			2.1		nC
Q _{oss}	Output Charge	$V_{DS} = 15V, V_{GS} = 0V$		36		nC
t _{d(on)}	Turn On Delay Time			9		ns
t _r	Rise Time	$V_{DS} = 12.5V, V_{GS} = 4.5V,$		15		ns
$t_{d(off)}$	Turn Off Delay Time	$I_D = 25A$, $R_G = 2\Omega$		27		ns
t _f	Fall Time			17		ns
Diode C	haracteristics					
V _{SD}	Diode Forward Voltage	I _{SD} = 25A, V _{GS} = 0V		0.8	1	V
Q _{rr}	Reverse Recovery Charge	$V_{DD} = 13V$, $I_F = 25A$, $di/dt = 300A/\mu s$		33		nC
t _{rr}	Reverse Recovery Time	$V_{DD} = 13V$, $I_F = 25A$, $di/dt = 300A/\mu s$		32		ns

THERMAL CHARACTERISTICS

 $(T_A = 25$ °C unless otherwise stated)

	PARAMETER	MIN	TYP	MAX	UNIT
R ₀ JC	Thermal Resistance Junction to Case ⁽¹⁾			1.1	°C/W
R _{θJA}	Thermal Resistance Junction to Ambient ⁽¹⁾ (2)			48	°C/W

⁽¹⁾ $R_{\theta JC}$ is determined with the device mounted on a 1 inch square 2 oz. Cu pad on a 1.5 x 1.5 in .060 inch thick FR4 board. $R_{\theta JC}$ is specified by design while $R_{\theta JA}$ is determined by the user's board design.

2

Product Folder Link(s): CSD16321Q5

⁽²⁾ Device mounted on FR4 Material with 1 inch² of 2 oz. Cu.

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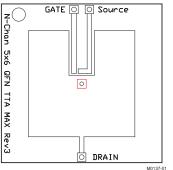
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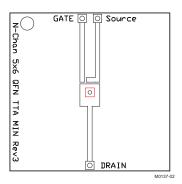
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Max $R_{\theta JA} = 48^{\circ}$ C/W when mounted on 1 inch² of 2 oz. Cu.



Max $R_{\theta JA} = 115^{\circ}\text{C/W}$ when mounted on minimum pad area of 2 oz. Cu.

TYPICAL MOSFET CHARACTERISTICS

(T_A = 25°C unless otherwise stated)

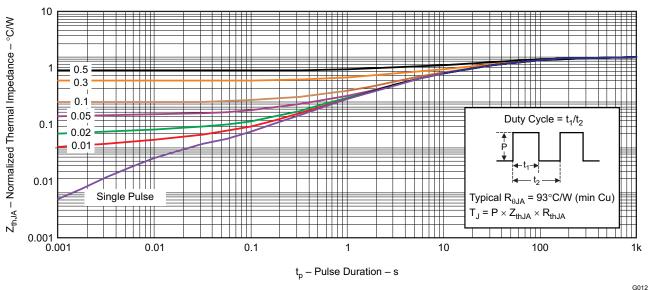


Figure 1. Transient Thermal Impedance

G012

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TYPICAL MOSFET CHARACTERISTICS (continued)

(T_A = 25°C unless otherwise stated)

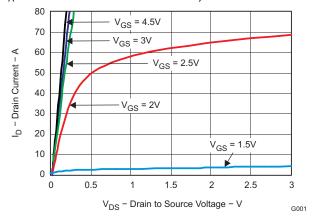


Figure 2. Saturation Characteristics

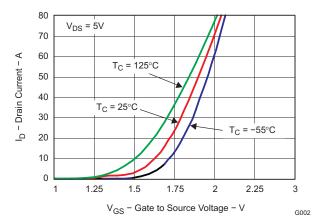


Figure 3. Transfer Characteristics

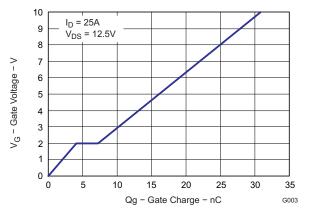


Figure 4. Gate Charge

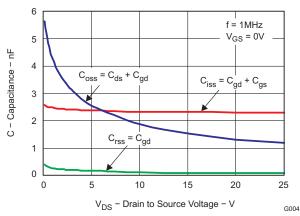


Figure 5. Capacitance

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TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

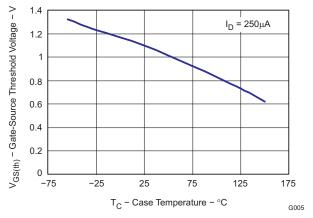


Figure 6. Threshold Voltage vs. Temperature

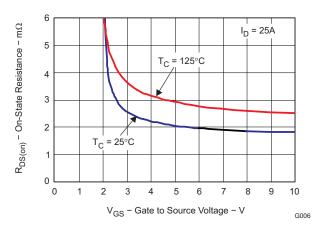


Figure 7. On Resistance vs. Gate Voltage

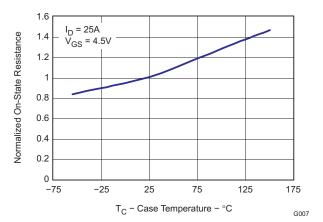


Figure 8. On Resistance vs. Temperature

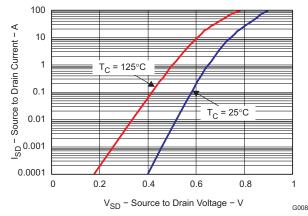


Figure 9. Typical Diode Forward Voltage

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TYPICAL MOSFET CHARACTERISTICS (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

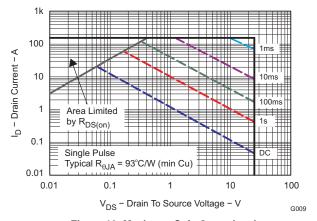


Figure 10. Maximum Safe Operating Area

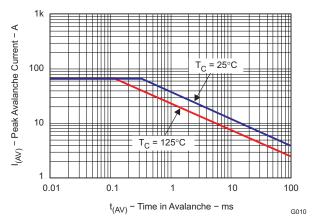


Figure 11. Single Pulse Unclamped Inductive Switching

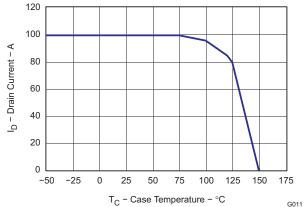


Figure 12. Maximum Drain Current vs. Temperature

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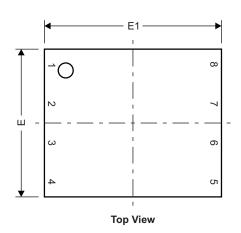
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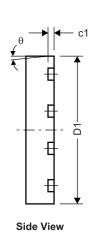
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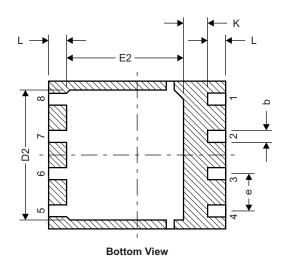
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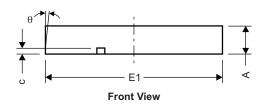
MECHANICAL DATA

Q5 Package Dimensions









M0140-01

DIM	MILLIN	METERS	INC	HES
DIM	MIN	MAX	MIN	MAX
А	0.950	1.050	0.037	0.039
b	0.360	0.460	0.014	0.018
С	0.150	0.250	0.006	0.010
c1	0.150	0.250	0.006	0.010
D1	4.900 5.100		0.193	0.201
D2	4.320	4.320 4.520		0.178
E	4.900	5.100	0.193	0.201
E1	5.900	6.100	0.232	0.240
E2	3.920	3.920 4.12 0.154		
е	1.27	TYP	0.0	050
K	K 0.760		0.030	
L	0.510	0.710	0.020	0.028
θ	0.00			

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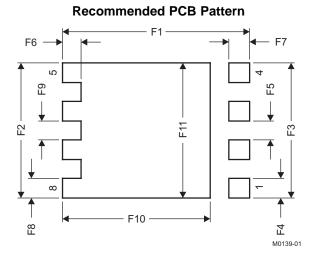
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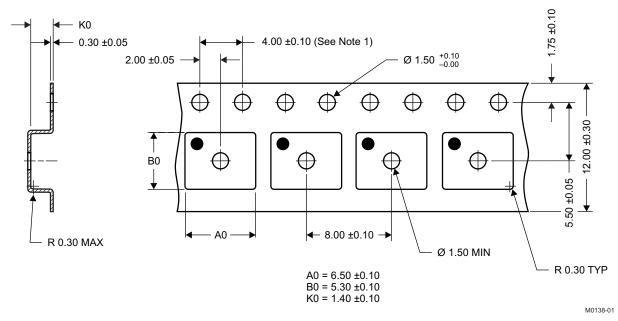
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DIM	MILLIM	ETERS	INC	HES
DIN	MIN	MAX	MIN	MAX
F1	6.205	6.305	0.244	0.248
F2	4.460	4.560	0.176	0.180
F3	4.460	4.560	0.176	0.180
F4	0.650	0.700	0.026	0.028
F5	0.620	0.670	0.024	0.026
F6	0.630	0.680	0.025	0.027
F7	0.700	0.800	0.028	0.031
F8	0.650	0.700	0.026	0.028
F9	0.620	0.670	0.024	0.026
F10	4.900	5.000	0.193	0.197
F11	4.460	4.560	0.176	0.180

For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

Q5 Tape and Reel Information



Notes:

- 1. 10 sprocket hole pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1mm IN 100mm, noncumulative over 250mm
- 3. Material:black static dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified)
- 5. ThickNess: 0.30 ±0.05mm
- 6. MSL1 260°C (IR and Convection) PbF Reflow Compatible



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REVISION HISTORY

С	changes from Original (August 2009) to Revision A	Page
•	Changed the labels on the Top View pinout image	1
•	Changed Note 1 of the ABSOLUTE MAXIMUM RATINGS From: $R_{\theta JA} = 39^{\circ}\text{C/W}$ To: Typical $R_{\theta JA} = 39^{\circ}\text{C/W}$	1
•	Changed Figure 1 text From: R _{θJA} = 92°C/W To: Typical R _{θJA} = 93°C/W	3
•	Changed Figure 10 text From: R _{0JA} = 92°C/W To: Typical R _{0JA} = 93°C/W	6
<u>.</u>	Changed Figure 11 X-axis values	6
С	changes from Revision A (Jaunary 2010) to Revision B	Page
•	Changed R _{DS(on)} - V _{GS} = 3V, I _D = 25A MAX value From: 3.5 To: 3.8	2
•	Deleted the Package Marking Information section	8



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PACKAGE OPTION ADDENDUM

7-Jan-2016

PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package	Pins	Package	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
CSD16321Q5	ACTIVE	VSON-CLIP	DQH	8	2500	Pb-Free (RoHS Exempt)	CU SN	Level-1-260C-UNLIM	-55 to 150	CSD16321	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design. PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details. **TBD:** The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): Ti's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between

the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device
- (6) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

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Addendum-Page 2



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